# Abstracts

## A 12-15 GHz High Gain Amplifier Design Using Submicron Gate GaAs Field Effect Transistors

*M.G. Walker and E.J. Crescenzi, Jr.. "A 12-15 GHz High Gain Amplifier Design Using Submicron Gate GaAs Field Effect Transistors." 1976 MTT-S International Microwave Symposium Digest of Technical Papers 76.1 (1976 [MWSYM]): 107-110.*

An amplifier covering 12-15 GHz with 22 dB gain and less than 5.0 dB noise figure using GsAs FETs with submicron gate length was constructed. Techniques used for device characterization and amplifier circuit synthesis along with measured data are presented.

❑ Return to main document.